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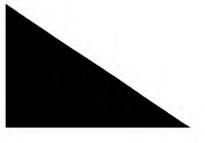
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APPLICATION NO. FILING DATE FIRST NAMED INVENTOR ATTORNEY DOCKET NO 09/517,705 03/02/00 LIANG \Box 042390.P5771 **EXAMINER** MM91/0815 Blakely Sokoloff Taylor & Zafman LLP PAPER NUMBER ART UNIT 12400 Wilshire Boulevard 7th Floor Los Angeles CA 90025 2811 **DATE MAILED:**

Please find below and/or attached an Office communication concerning this application or proceeding.

Commissioner of Patents and Trademarks

08/15/01



		Application No.	Applicant(s)
•	•	09/517,705	LIANG ET AL.
Office Action Summary		Examiner	Art Unit
		Steven Loke	2811
Period fo	The MAILING DATE of this communication or Reply	appears on the cover sheet w	ith the correspondence address
THE I - External after - If the - If NC - Failurian - Any r	ORTENED STATUTORY PERIOD FOR REMAILING DATE OF THIS COMMUNICATION asions of time may be available under the provisions of 37 CF SIX (6) MONTHS from the mailing date of this communication period for reply specified above is less than thirty (30) days, a period for reply is specified above, the maximum statutory per to reply within the set or extended period for reply will, by seply received by the Office later than three months after the new part of the provided patent term adjustment. See 37 CFR 1.704(b).	DN. R 1.136(a). In no event, however, may a r n. a reply within the statutory minimum of thir eriod will apply and will expire SIX (6) MON tatute, cause the application to become AE	reply be timely filed ty (30) days will be considered timely. ITHS from the mailing date of this communication. BANDONED (35 U.S.C. § 133).
1)[\]	Responsive to communication(s) filed on	05 January 2001 .	
2a) <u></u>	This action is FINAL . 2b)⊠	This action is non-final.	
3)	Since this application is in condition for al closed in accordance with the practice un		
Dispositi	on of Claims		
4) 🖂	Claim(s) 1 and 2 is/are pending in the app	olication.	
	4a) Of the above claim(s) is/are with	drawn from consideration.	
5)	Claim(s) is/are allowed.		
6)⊠	Claim(s) 1 and 2 is/are rejected.		
7)	Claim(s) is/are objected to.		
8)[Claim(s) are subject to restriction a	nd/or election requirement.	
Applicat	on Papers		
9)[The specification is objected to by the Exar	niñer.	
10) 🗌	The drawing(s) filed on is/are: a)□ a	accepted or b) objected to by t	he Examiner.
	Applicant may not request that any objection	to the drawing(s) be held in abey	ance. See 37 CFR 1.85(a).
11) 🗌	The proposed drawing correction filed on $_$	is: a)□ approved b)□ c	lisapproved by the Examiner.
	If approved, corrected drawings are required	in reply to this Office action.	
12)	The oath or declaration is objected to by the	e Examiner.	
Priority (ınder 35 U.S.C. §§ 119 and 120		
13)	Acknowledgment is made of a claim for for	reign priority under 35 U.S.C.	§ 119(a)-(d) or (f).
a)	☐ All b)☐ Some * c)☐ None of:		
	1. Certified copies of the priority docum	nents have been received.	
	2. Certified copies of the priority documents	nents have been received in A	Application No
* 5	3. Copies of the certified copies of the application from the International Gee the attached detailed Office action for a	l Bureau (PCT Rule 17.2(a)).	
	acknowledgment is made of a claim for dom	•	
а) The translation of the foreign language Acknowledgment is made of a claim for don	provisional application has b	een received.
Attachmen		and processing united to the control of the control	. gg .===
1) Notice 2) Notice	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948 nation Disclosure Statement(s) (PTO-1449) Paper No	5) Notice of	Summary (PTO-413) Paper No(s) Informal Patent Application (PTO-152)

Application/Control Number: 09/517,705

Art Unit: 2811

Since the supplemental preliminary amendment filed on 1/5/01 has canceled the method claims 3-15, the restriction mailed on 2/13/01 is withdrawn from the application.

The abstract of the disclosure is objected to because the abstract should disclose the structure of the device instead of the method to make the device. Correction is required.

The disclosure is objected to because of the following informalities:

In page 9, line 26, change "thickness a" to "a thickness".

Since the written description (page 12, lines 10-11) discloses molybdenum silicide has a Fermi level of 4.25 eV (N-type), it is unclear why molybdenum silicide is used as a gate electrode for PMOS device (page 15, lines 22-26).

Appropriate correction is required.

Claims 1 and 2 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

In claim 1, lines 2-3, "a first metal gate electrode overlying a over a first gate dielectric" is unclear whether it is being referred to "a first metal gate electrode overlying a first gate dielectric".

In claim 2, line 1, "The integrated circuit device" has no antecedent basis.

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

⁽b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Application/Control Number: 09/517,705

Art Unit: 2811

Claims 1 and 2 are rejected under 35 U.S.C. 102(b) as being clearly anticipated by Dash et al.

In regards to claim 1, Dash et al. shows all the elements of the claimed invention in fig. 9. It is a circuit device comprising: a first transistor (NMOS) including a first metal gate electrode [56] made of aluminum overlying a first gate dielectric [14'] on a first area of a semiconductor substrate and having a work function (4.1 eV) corresponding to the work function of the N-type silicon; and a second transistor (PMOS) complementary to the first transistor including a second metal gate electrode [50] made of platinum silicide over a second gate dielectric [14"] on a second area of a semiconductor substrate and having a work function (5.7 eV) corresponding to the work function of the P-type silicon.

In regards to claim 2, Dash et al. discloses the first metal gate electrode [56] (aluminum) is a pure metal.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Steven Loke whose telephone number is (703) 308-4920. The examiner can normally be reached on 7:45 am to 5:15 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on (703) 308-2772. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7722 for regular communications and (703) 308-7722 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Application/Control Number: 09/517,705

Art Unit: 2811

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August 12, 2001

Steven Loke Primary Examiner

Steven Sohe